









CEB12P10

-100V ▲ 260mΩ ▲ -11A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type
P-channel enhancement mode
UL94V-0 rated flame retardant epoxy
TO263 (D²PAK) package ▲ MSL 3
Super high dense cell density for extremely low R_{DS(ON)}
High power and current handling capability

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-100V
Gate-Source Voltage	V _{GS}	±30V
Continuous Drain Current at T _C = 25°C	I _D	-11A
Pulsed Drain Current Note 1	I _{DM}	-44A
Maximum Power Dissipation at T _C = 25°C	P _D	75W
Power Dissipation Derating above 25°C	ΔP _D	0.5W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

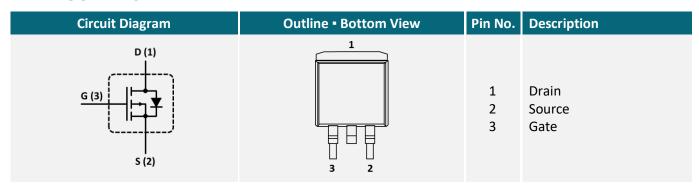
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	2°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH_JA}	62.5°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			+	Ŷ

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS \blacktriangle T_C = 25°C, unless otherwise noted

Item	Condition	Symbol N		Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV_DSS	-100			V
Zero Gate Voltage Drain Current	$V_{DS} = -100V$, $V_{GS} = 0V$	I _{DSS}			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -30V$, $V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250 \mu A$	$V_{GS(th)}$	-2		-4	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$, $I_D = -5.75A$	R _{DS(ON)}		260	315	mΩ
Forward Transconductance	$V_{DS} = -40V$, $I_{D} = -5.75A$	g FS		3.5		S
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1MHz$	C_{ISS}		625		pF
Output Capacitance	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		140		pF
Reverse Transfer Capacitance	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1MHz$		45		pF	
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = -50V, V_{GS} = -10V, I_{D} = -11A, $R_{G(ext)}$ = 25 Ω	$t_{\text{D(ON)}}$		15	30	ns
Turn-On Rise Time	V_{DD} = -50V, V_{GS} = -10V, I_{D} = -11A, $R_{G(ext)}$ = 25 Ω	t_R		12	25	ns
Turn-Off Delay Time	V_{DD} = -50V, V_{GS} = -10V, I_{D} = -11A, $R_{G(ext)}$ = 25 Ω	$t_{D(OFF)}$		31	60	ns
Turn-Off Fall Time	V_{DD} = -50V, V_{GS} = -10V, I_{D} = -11A, $R_{G(ext)}$ = 25 Ω	t _F		31	60	ns
Total Gate Charge	V_{DS} = -80V, V_{GS} = -10V, I_D = -11A	Q_{G}		15.6	20	nC
Gate Source Charge	$V_{DS} = -80V$, $V_{GS} = -10V$, $I_D = -11A$	Q_{GS}		3.6		nC
Gate Drain Charge	$V_{DS} = -80V$, $V_{GS} = -10V$, $I_{D} = -11A$	\mathbf{Q}_{GD}		6		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode		I _S			-11	Α
Forward Current Drain-Source Diode						
Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = -11A$	V_{SD}			-1.5	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

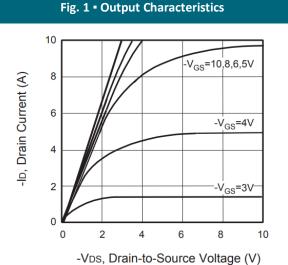


Fig. 2 • Transfer Characteristics

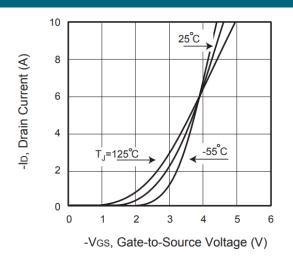


Fig. 3 • Capacitance

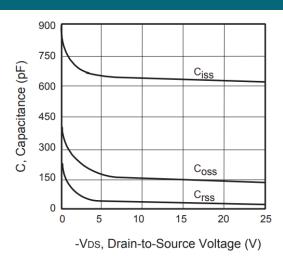


Fig. 4 • On-Resistance Variation with Temperature

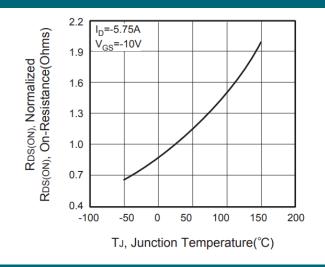


Fig. 5 • Gate Threshold Variation with Temperature

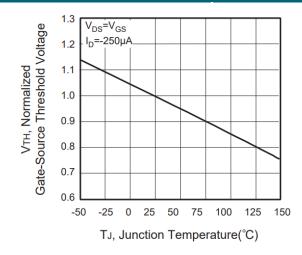
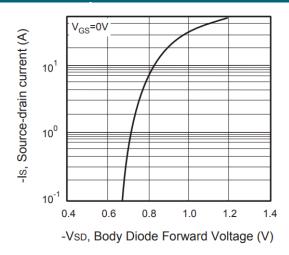
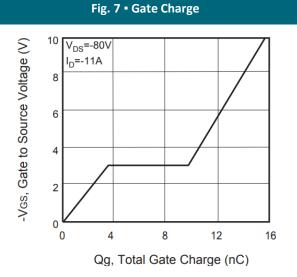


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



10²
R_{DS(ON)}Limit
100µs
100 100
T_C=25°C
T_J=175°C
Single Pulse

Fig. 8 • Maximum Safe Operating Area

Fig. 9 • Switching Test Circuit

Fig. 10 - Switching Waveforms

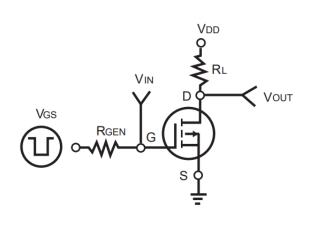
-VDS, Drain-Source Voltage (V)

10²

10³

10¹

10⁰



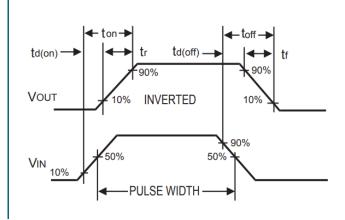
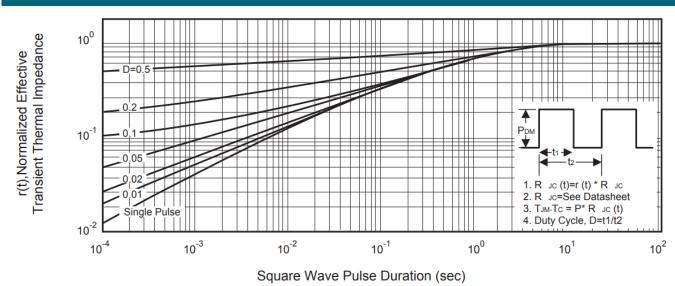


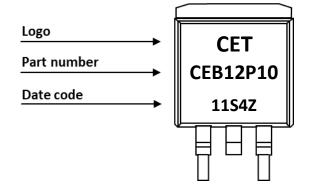
Fig. 11 - Normalized Thermal Transient Impedance Curve



MGT A Manufacturer Group of Technolog

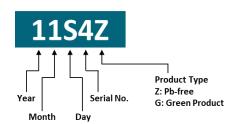


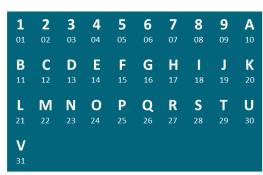
PART MARKING



DATE CODE

Example: 11S4Z



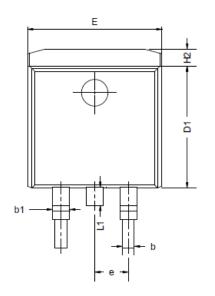


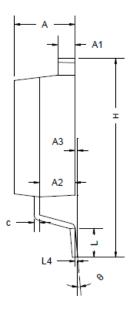
Coding list for "Day"

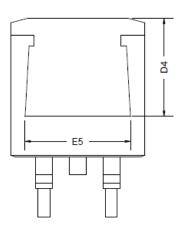


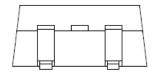


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	A3 0.00		0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

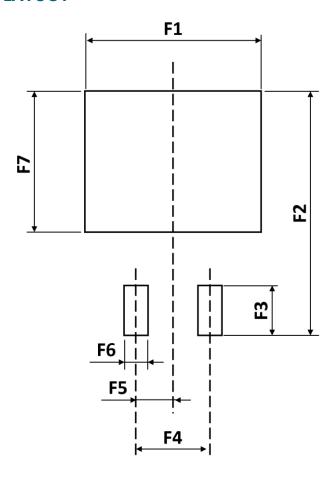
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)				
Е	9.86	10.16	10.36				
E5	7.06	-	-				
е	2.54 BSC						
Н	14.70	15.10	15.50				
H2	1.07	1.27	1.47				
L	2.00	2.30	2.60				
L1	1.40	1.55	1.70				
L4	0.25 BSC						
θ	0°	5°	9°				

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB12P10	TO263 (D ² PAK)	Reel	800pcs	800pcs	6,400pcs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	12.20	-	
F2	-	16.90	-	
F3	-	2.54	-	
F4	-	5.08	-	

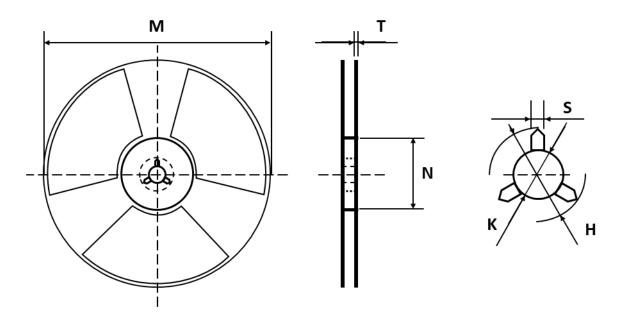
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

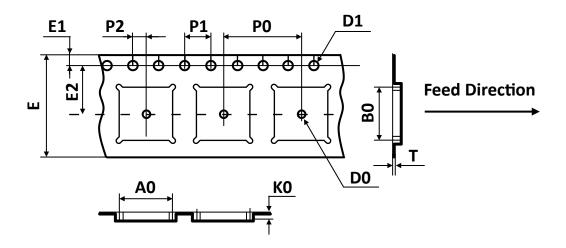


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		12.00	±0.50	±0.20	±0.50		-0.20

TAPE DIMENSIONS ▲ All dimensions in mm

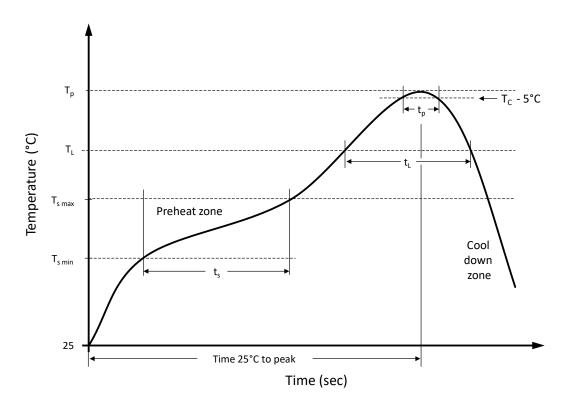


Pac	ckage	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	Т
TC	0263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ²	² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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